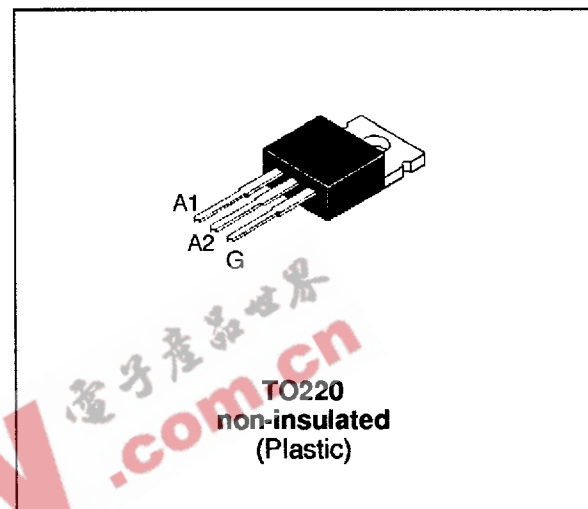


**STANDARD TRIACS**
**FEATURES**

- $I_{T(RMS)} = 25A$
- $V_{DRM} = 400V$  to  $800V$
- High surge current capability

**DESCRIPTION**

The T25xxxH series of triacs uses a high performance MESA GLASS technology. These parts are intended for general purpose switching and phase control applications.


**ABSOLUTE RATINGS (limiting values)**

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	$T_c = 80\text{ }^\circ\text{C}$ 25	A
$I_{TSM}$	Non repetitive surge peak on-state current ( $T_j$ initial = $25\text{ }^\circ\text{C}$ )	$t_p = 8.3\text{ ms}$	262
		$t_p = 10\text{ ms}$	250
$I^2t$	$I^2t$ Value for fusing	$t_p = 10\text{ ms}$ 312	$A^2s$
$di/dt$	Critical rate of rise of on-state current $I_G = 500\text{ mA}$ $di_G/dt = 1\text{ A}/\mu\text{s}$ .	Repetitive $F = 50\text{ Hz}$	10
		Non Repetitive	50
$T_{stg}$ $T_j$	Storage and operating junction temperature range	- 40, + 150 - 40, + 125	$^\circ\text{C}$
$T_l$	Maximum lead temperature for soldering during 10s at 4.5mm from case	260	$^\circ\text{C}$

Symbol	Parameter	Voltage				Unit
		D	M	S	N	
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage $T_j = 125\text{ }^\circ\text{C}$	400	600	700	800	V

T25xxxH

**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	60	°C/W
Rth(j-c)	Junction to case for D.C	2	°C/W
Rth(j-c)	Junction to case for A.C 360° conduction angle (F=50Hz)	1.5	°C/W

**GATE CHARACTERISTICS** (maximum values)

$P_G (AV) = 1 W$   $P_{GM} = 10 W$  ( $t_p = 20 \mu s$ )  $I_{GM} = 4 A$  ( $t_p = 20 \mu s$ )

**ELECTRICAL CHARACTERISTICS**

Symbol	Test Conditions		Quadrant		Sensitivity		Unit
					12	13	
$I_{GT}$	$V_D = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	I-II-III	MAX	50	50	mA
			IV	MAX	50	75	
$V_{GT}$	$V_D = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	I-II-III-IV	MAX	1.5		V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3k\Omega$	$T_j = 125^\circ C$	I-II-III-IV	MIN	0.2		V
$t_{gt}$	$V_D = V_{DRM}$ $I_G = 500mA$ $I_T = 35A$ $di_G/dt = 3A/\mu s$	$T_j = 25^\circ C$	I-II-III-IV	TYP	2		$\mu s$
$I_H^*$	$I_T = 250 mA$ Gate open	$T_j = 25^\circ C$		MAX	50	75	mA
$I_L$	$I_G = 1.2 I_{GT}$	$T_j = 25^\circ C$	I-III-IV	TYP	50	75	mA
			II	TYP	100	150	
$V_{TM}^*$	$I_{TM} = 35A$ $t_p = 380\mu s$	$T_j = 25^\circ C$		MAX	1.5		V
$I_{DRM}$ $I_{RRM}$	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$		MAX	10		$\mu A$
		$T_j = 110^\circ C$		MAX	3		mA
$dV/dt^*$	$V_D = 67\% V_{DRM}$ Gate open	$T_j = 110^\circ C$		MIN	500		V/ $\mu s$
$(dV/dt)c^*$	$(di/dt)c = 11 A/ms$	$T_j = 110^\circ C$		MIN	5	10	V/ $\mu s$

\* For either polarity of electrode A<sub>2</sub> voltage with reference to electrode A<sub>1</sub>

**ORDERING INFORMATION**

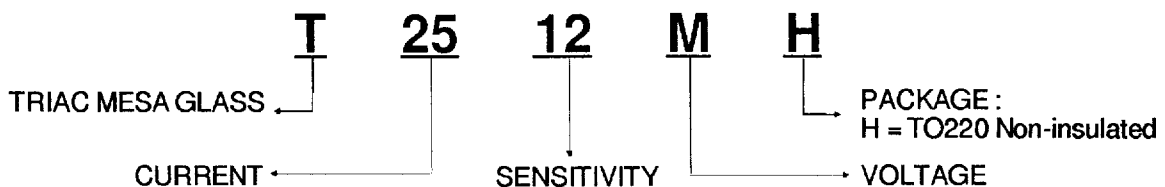


Fig.1 : Maximum RMS power dissipation versus RMS on-state current.

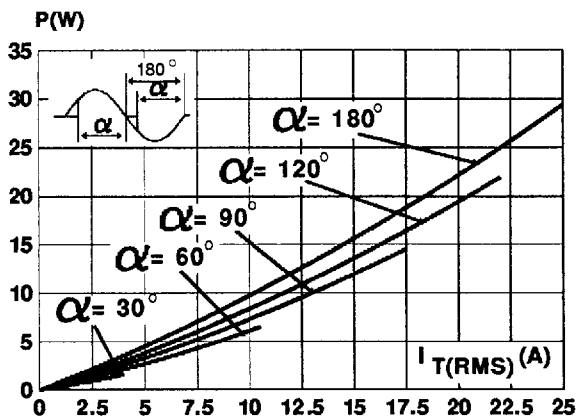


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperature (Tamb and Tcase) for different thermal resistances heatsink + contact.

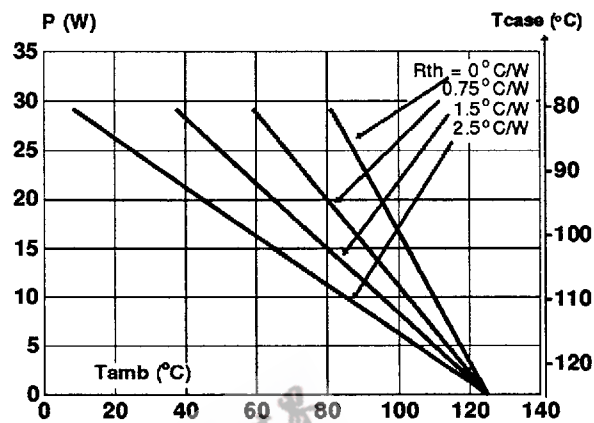


Fig.3 : RMS on-state current versus case temperature.

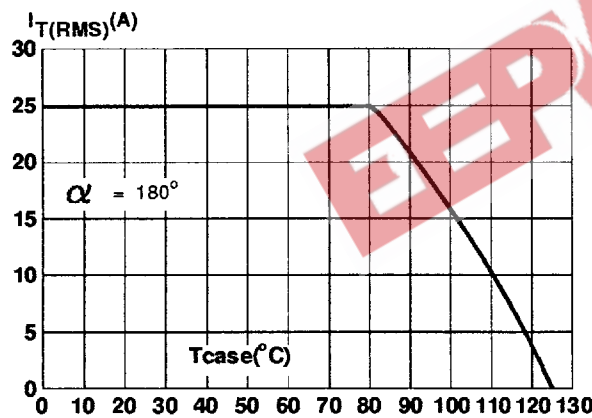


Fig.4 : Relative variation of thermal impedance versus pulse duration.

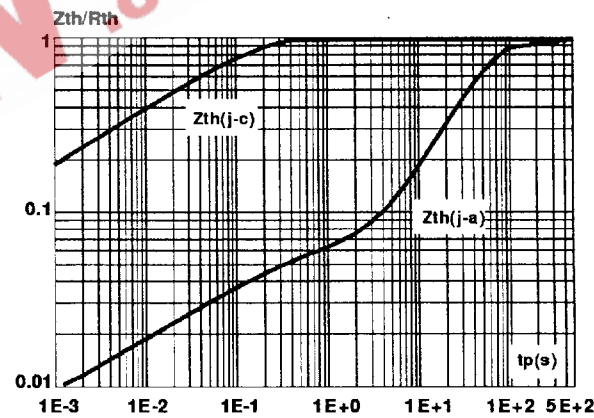


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

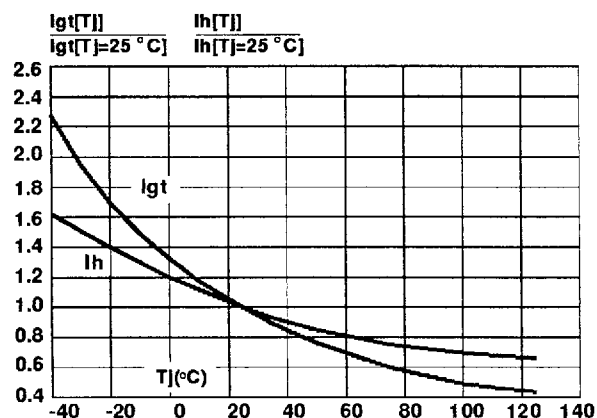
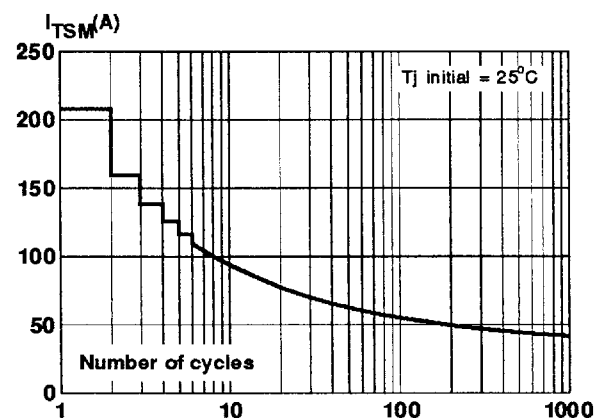


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.



T25xxxH

Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $t \leq 10\text{ms}$ , and corresponding value of  $I^2t$ .

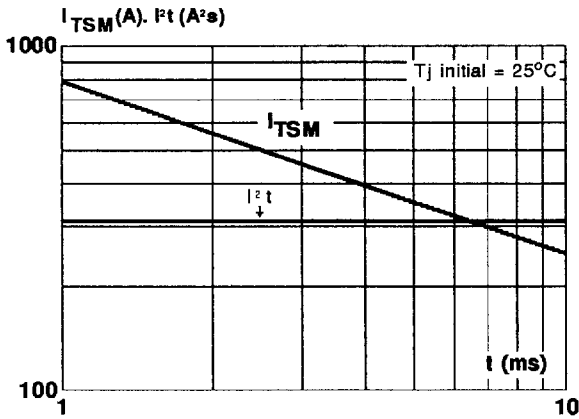
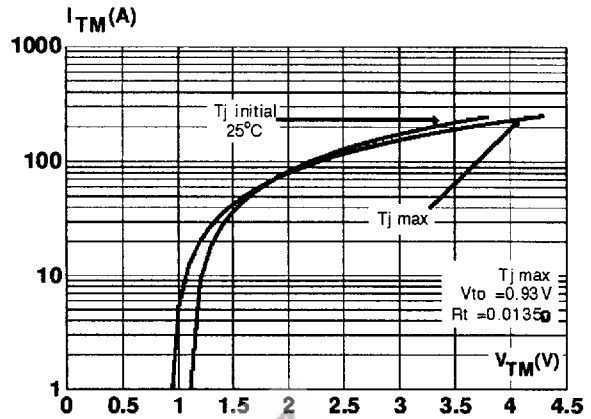


Fig.8 : On-state characteristics (maximum values).



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**PACKAGE MECHANICAL DATA**  
 TO220 Non-insulated (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A			10.3			0.406
B		6.3	6.5	0.248	0.256	
C			9.1			0.358
D		12.7			0.500	
F			4.2			0.165
G			3.0			0.118
H		4.5	4.7		0.177	0.185
I		3.53	3.66		0.139	0.144
J		1.2	1.3		0.047	0.051
L			0.9			0.035
M	2.7			0.106		
N			5.3			0.209
N1	2.54			0.100		
O		1.2	1.4		0.047	0.055
P			1.15			0.045

Marking : type number  
 Weight : 1.8 g

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